

Turbo 2 ultrafast high voltage rectifier

Datasheet – production data

Features

- Ultrafast switching
- Low reverse recovery current
- Low thermal resistance
- Reduces switching losses
- ECOPACK[®]2 compliant component
- Ribbon bonding for more robustness

Description

The STTH60W02CW uses ST Turbo 2, 200 V technology. It is especially suited for use in DC/DC and DC/AC converters in secondary stage of MIG/MMA/TIG welding machine. Housed in ST's TO-247, this device offers high power integration for all welding machines and industrial applications.

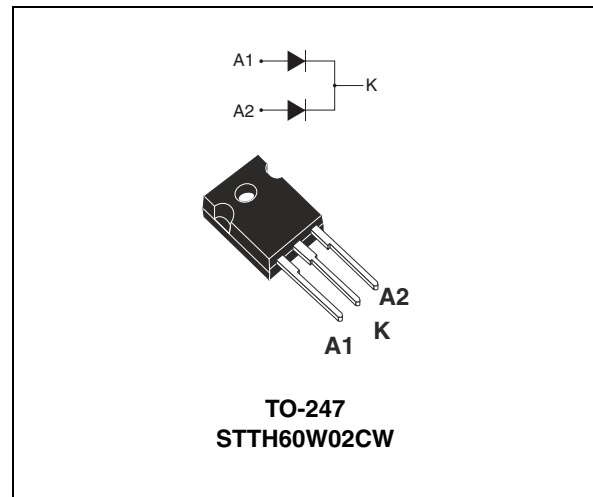


Table 1. Device summary

Symbol	Value
$I_{F(AV)}$	2 x 30 A
V_{RRM}	200 V
t_{rr} (typ)	24 ns
T_j (max)	175 °C
V_F (typ)	0.85 V

1 Characteristics

Table 2. Absolute ratings (limiting values, at 25 °C, unless otherwise specified, per diode)

Symbol	Parameter		Value	Unit	
V_{RRM}	Repetitive peak reverse voltage		200	V	
$I_{F(RMS)}$	Forward rms current		45	A	
$I_{F(AV)}$	Average forward current, $\delta = 0.5$	$T_c = 125\text{ °C}$	Per diode	30	A
		$T_c = 115\text{ °C}$	Per device	60	
I_{FSM}	Surge non repetitive forward current	$t_p = 10\text{ ms sinusoidal}$	250	A	
T_{stg}	Storage temperature range		-65 to + 175	°C	
T_j	Maximum operating junction temperature		+ 175	°C	

Table 3. Thermal resistance

Symbol	Parameter		Value	Unit
$R_{th(j-c)}$	Junction to case	Per diode	1.3	°C / W
		Total	0.8	
$R_{th(c)}$	Coupling		0.3	°C / W

When diodes 1 and 2 are used simultaneously:

$$T_j(\text{diode 1}) = P(\text{diode 1}) \times R_{th(j-c)}(\text{per diode}) + P(\text{diode 2}) \times R_{th(c)}$$

Table 4. Static electrical characteristics (per diode)

Symbol	Parameter	Test conditions		Min.	Typ	Max.	Unit
$I_R^{(1)}$	Reverse leakage current	$T_j = 25\text{ °C}$	$V_R = V_{RRM}$			10	μA
		$T_j = 125\text{ °C}$			10	100	
$V_F^{(2)}$	Forward voltage drop	$T_j = 25\text{ °C}$	$I_F = 30\text{ A}$			1.15	V
		$T_j = 150\text{ °C}$			0.85	1.0	
		$T_j = 25\text{ °C}$	$I_F = 60\text{ A}$			1.35	
		$T_j = 150\text{ °C}$			1.05	1.25	

1. Pulse test: $t_p = 5\text{ ms}$, $\delta < 2\%$

2. Pulse test: $t_p = 380\text{ }\mu\text{s}$, $\delta < 2\%$

To evaluate the conduction losses use the following equation:

$$P = 0.75 \times I_{F(AV)} + 0.0083 I_{F(RMS)}^2$$

Table 5. Dynamic electrical characteristics (per diode)

Symbol	Parameter	Test conditions		Min.	Typ	Max.	Unit
I_{RM}	Reverse recovery current	$T_j = 125\text{ }^\circ\text{C}$	$I_F = 30\text{ A}, V_R = 160\text{ V}$ $di_F/dt = -200\text{ A}/\mu\text{s}$		8	10.5	A
Q_{RR}	Reverse recovery charge				220		nC
S_{factor}	Softness factor				0.3		
t_{rr}	Reverse recovery time	$T_j = 25\text{ }^\circ\text{C}$	$I_F = 1\text{ A}, V_R = 30\text{ V}$ $di_F/dt = -100\text{ A}/\mu\text{s}$		24	30	ns
t_{fr}	Forward recovery time	$T_j = 25\text{ }^\circ\text{C}$	$I_F = 30\text{ A}, V_{FR} = 1.1\text{ V}$ $di_F/dt = 200\text{ A}/\mu\text{s}$			300	ns
V_{FP}	Forward recovery voltage	$T_j = 25\text{ }^\circ\text{C}$			2	3	V

Figure 1. Average forward power dissipation versus average forward current (per diode)

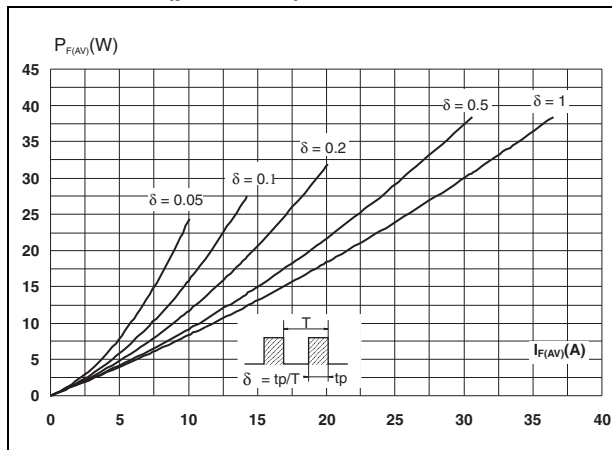


Figure 2. Forward voltage drop versus forward current (per diode)

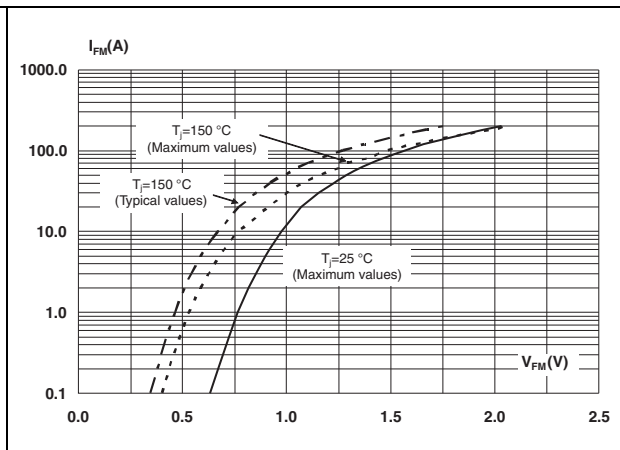


Figure 3. Relative variation of thermal impedance junction to case versus pulse duration

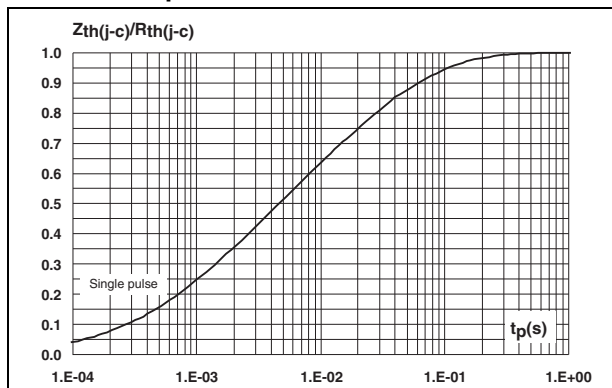


Figure 4. Peak reverse recovery current versus di_F/dt (typical values, per diode)

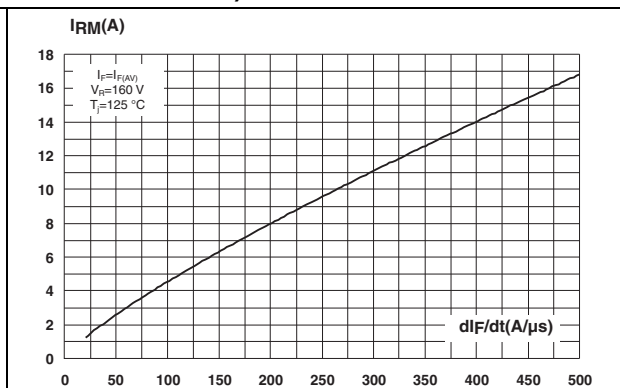


Figure 5. Reverse recovery time versus di_F/dt (typical values, per diode)

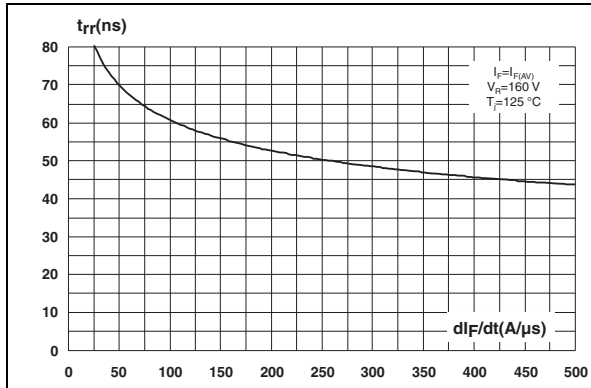


Figure 6. Reverse recovery charges versus di_F/dt (typical values, per diode)

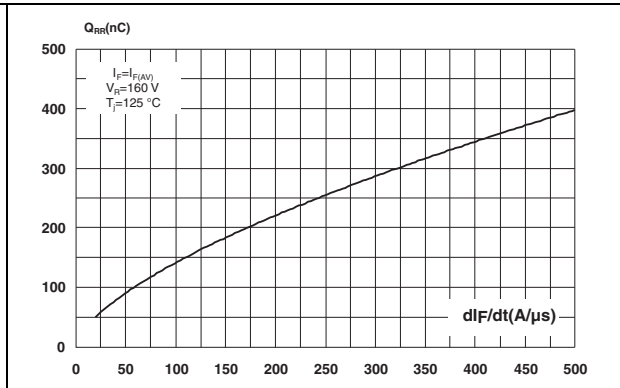


Figure 7. Reverse recovery softness factor versus di_F/dt (typical values, per diode)

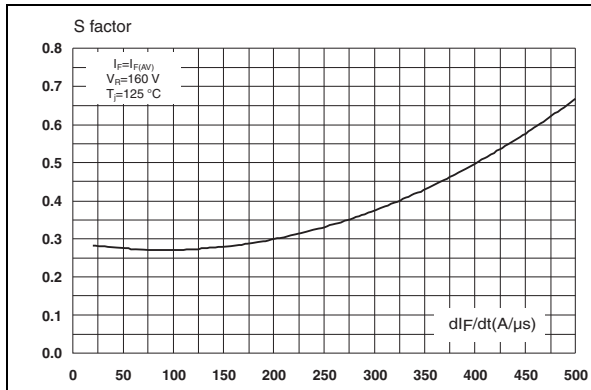


Figure 8. Relative variation of dynamic parameters versus junction temperature

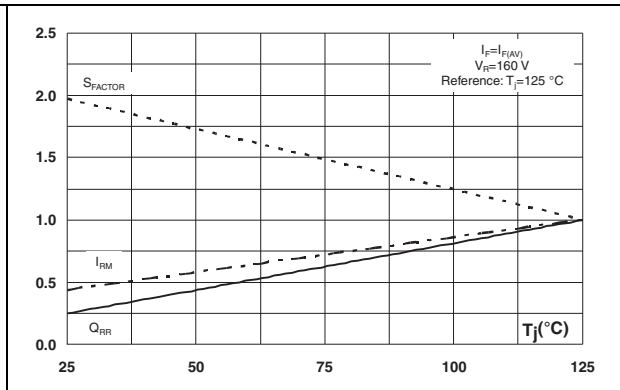


Figure 9. Transient peak forward voltage versus di_F/dt (typical values, per diode)

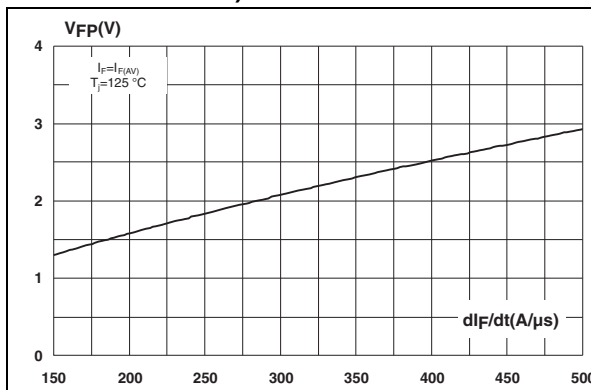


Figure 10. Forward recovery time versus di_F/dt (typical values, per diode)

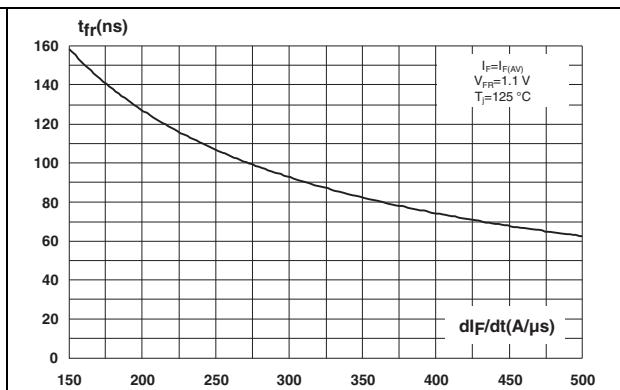
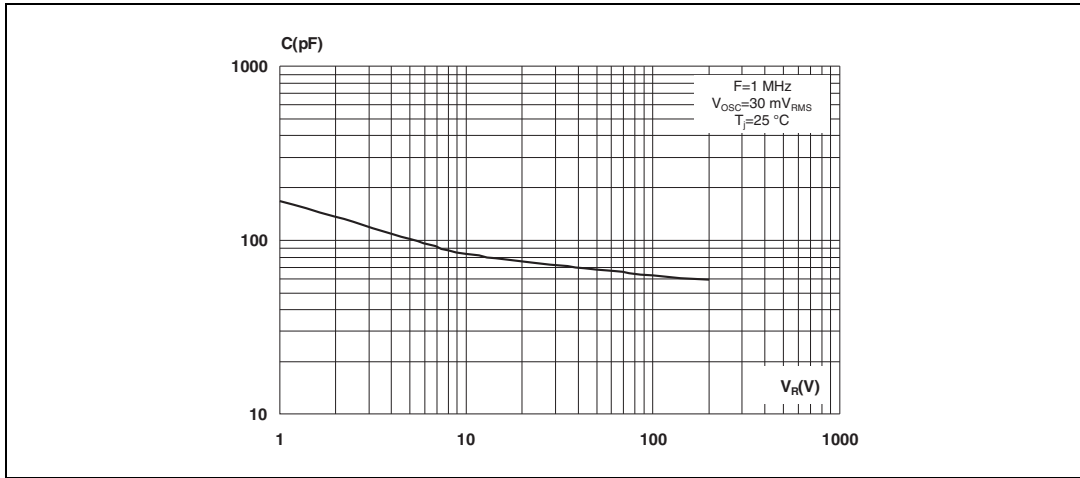


Figure 11. Junction capacitance versus reverse voltage applied (typical values, per diode)



2 Package information

- Epoxy meets UL94, V0
- Cooling method: by conduction (C)
- Recommended torque value: 0.55 N·m (1.0 N·m maximum)

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK® is an ST trademark.

Table 6. TO-247 dimensions

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.85		5.15	0.191		0.203
A1	2.20		2.60	0.086		0.102
b	1.00		1.40	0.039		0.055
b1	2.00		2.40	0.078		0.094
b2	3.00		3.40	0.118		0.133
c	0.40		0.80	0.015		0.031
D ⁽¹⁾	19.85		20.15	0.781		0.793
E	15.45		15.75	0.608		0.620
e	5.30	5.45	5.60	0.209	0.215	0.220
L	14.20		14.80	0.559		0.582
L1	3.70		4.30	0.145		0.169
L2	18.50 typ.			0.728 typ.		
∅P ⁽²⁾	3.55		3.65	0.139		0.143
∅R	4.50		5.50	0.177		0.217
S	5.30	5.50	5.70	0.209	0.216	0.224

1. Dimension D plus gate protrusion does not exceed 20.5 mm
2. Resin thickness around the mounting hole is not less than 0.9 mm

3 Ordering information

Table 7. Ordering information

Ordering type	Marking	Package	Weight	Base qty	Delivery mode
STTH60W02CW	STTH60W02CW	TO-247	4.46 g	50	Tube

4 Revision history

Table 8. Document revision history

Date	Revision	Changes
11-Oct-2012	1	First issue.

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